

Analysis of barrier inhomogeneities of P-type Al/4H-SiC Schottky barrier diodes

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Comparative results of low temperature annealing of lightly doped n-layers of silicon carbide irradiated by protons and electrons

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Nano- and Micro-Scale simulations of Ge/3C-SiC and Ge/4H-SiC NN-heterojunction diodes

Rashid, Muhammad Haroon; Koel, Ants; Rang, Toomas Silicon Carbide and Related Materials 2019 : 18th International Conference on Silicon Carbide and Related Materials 2019 (ICSCRM 2019), Kyoto, Japan, September 29 - October 4, 2019 Materials science forum 2020 / p. 490-496 <https://doi.org/10.4028/www.scientific.net/MSF.1004.490> [Conference proceedings at Scopus](#) [Article at Scopus](#)